[Proceeding] Cavity optimization of 1.3um InAs/InGaAs quantum dot passively mode-locked lasers

Original Citation:

Availability:
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Publisher:
SPIE-INT SOC OPTICAL ENGINEERING

Published version:
DOI:10.1117/12.981762

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Semiconductor Lasers and Applications V

Ning Hua Zhu
Jinmin Li
Frank H. Peters
Changyuan Yu
Editors

5–6 November 2012
Beijing, China

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SPIE

Volume 8552

Proceedings of SPIE 0277-786-786X, V.8552

SPIE is an international society advancing an interdisciplinary approach to the science and application of light.

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